
2SJ172

Silicon P-Channel MOS FET

HITACHI

November 1996

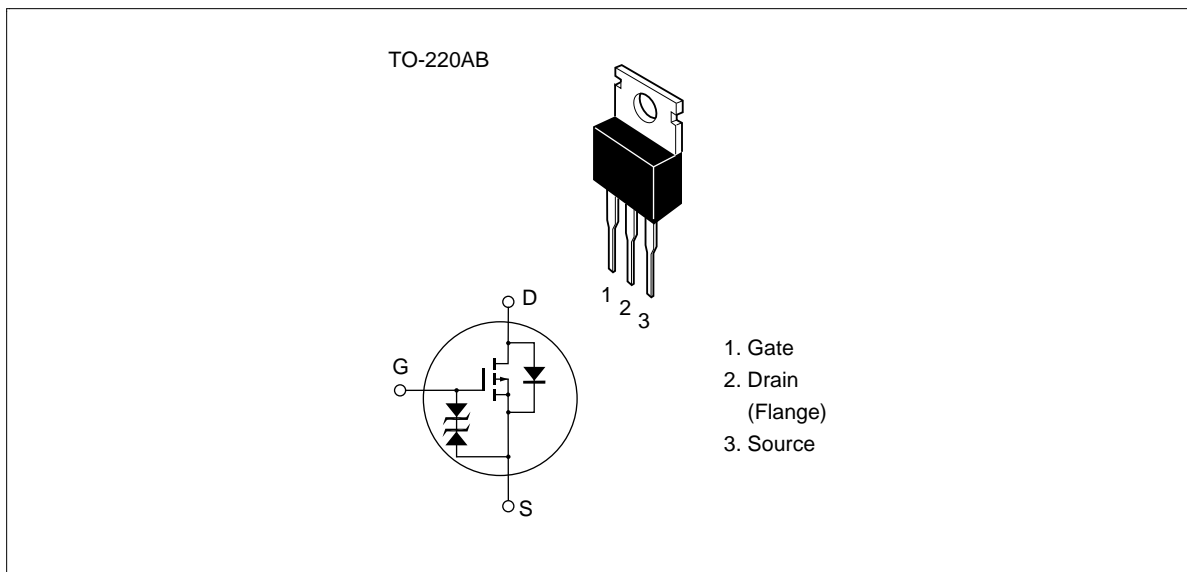
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline



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Absolute Maximum Ratings (Ta = 25°C)

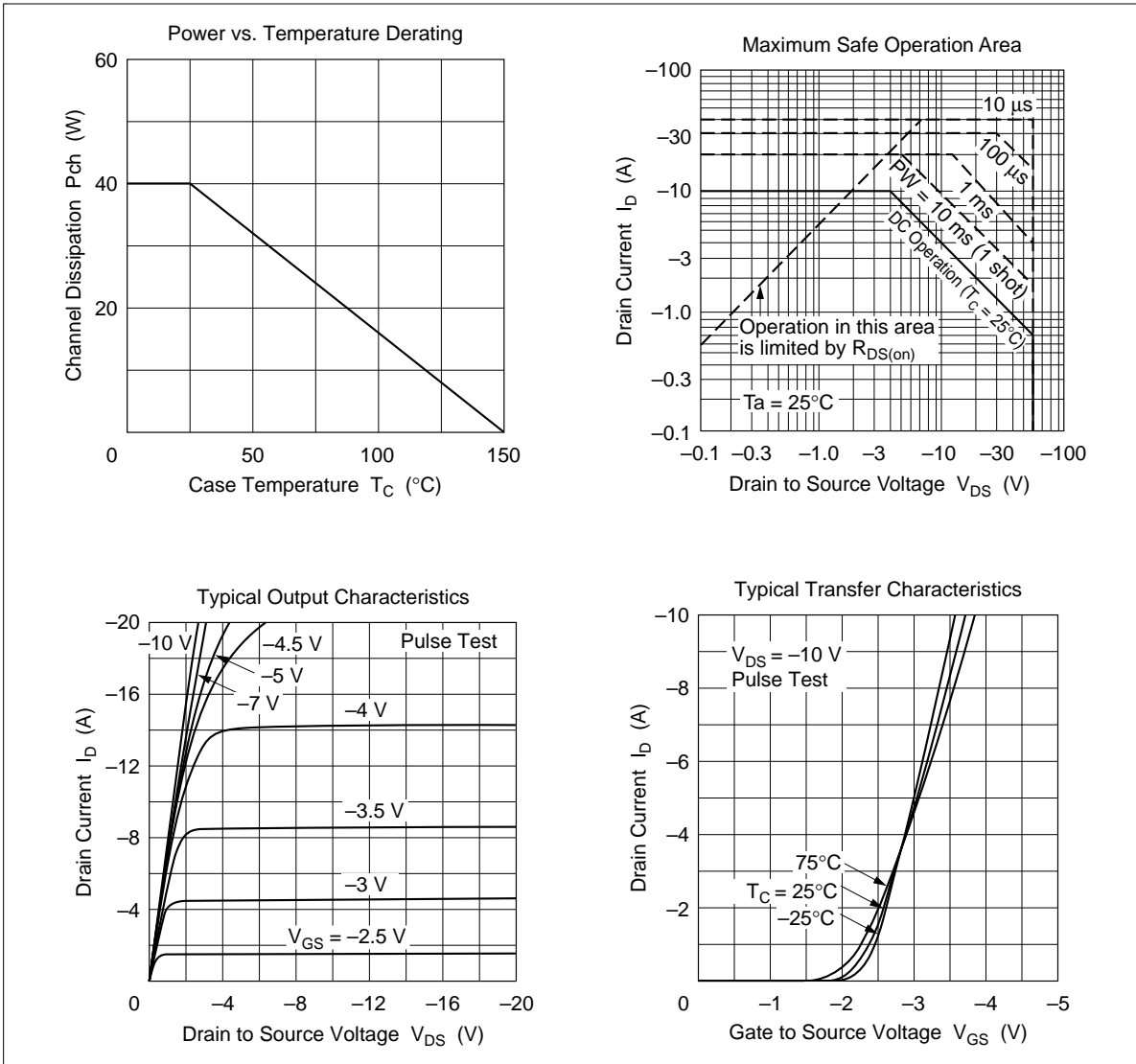
| Item | Symbol | Ratings | Unit |
|---|---------------------|-------------|------|
| Drain to source voltage | V_{DSS} | -60 | V |
| Gate to source voltage | V_{GSS} | ±20 | V |
| Drain current | I_D | -10 | A |
| Drain peak current | $I_{D(pulse)}^{*1}$ | -40 | A |
| Body to drain diode reverse drain current | I_{DR} | -10 | A |
| Channel dissipation | Pch*2 | 40 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

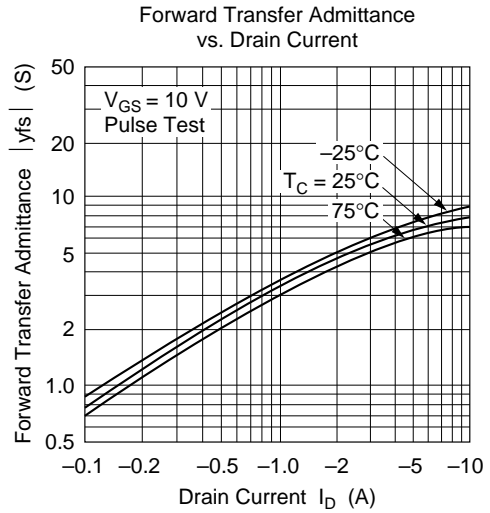
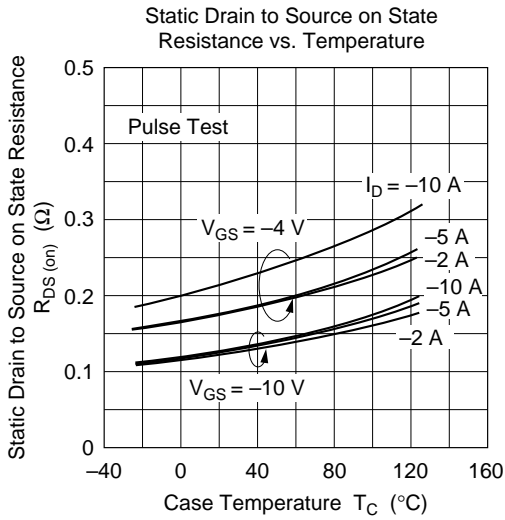
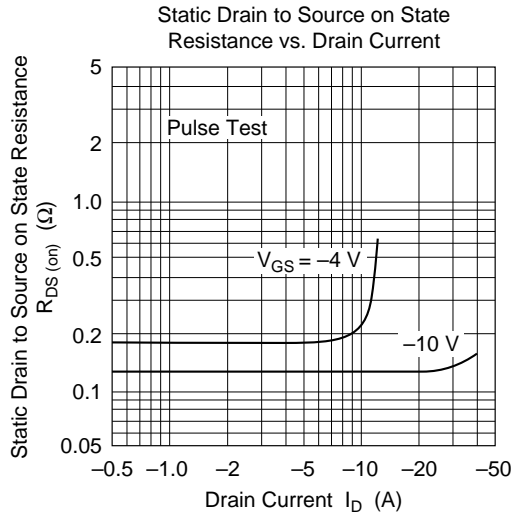
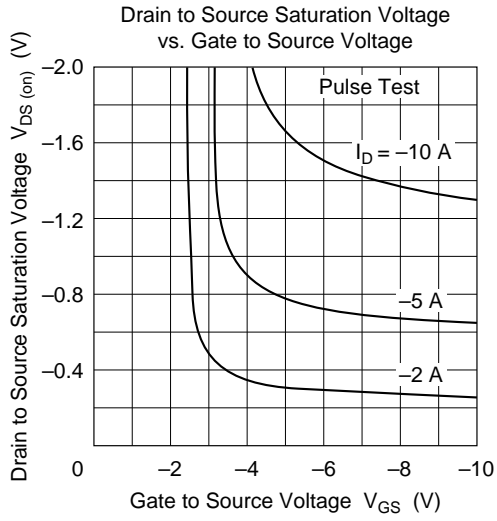
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$

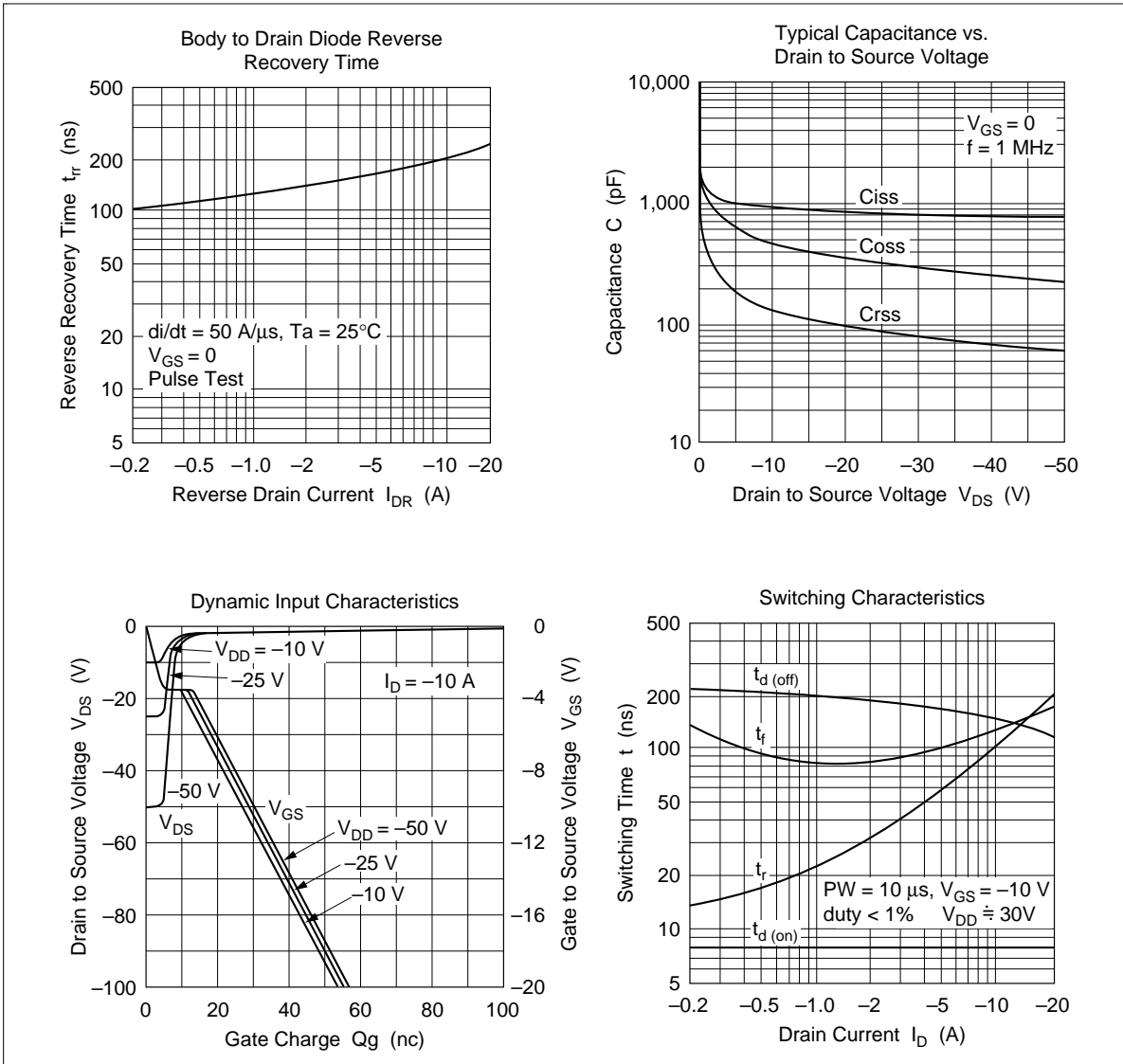
Electrical Characteristics (Ta = 25°C)

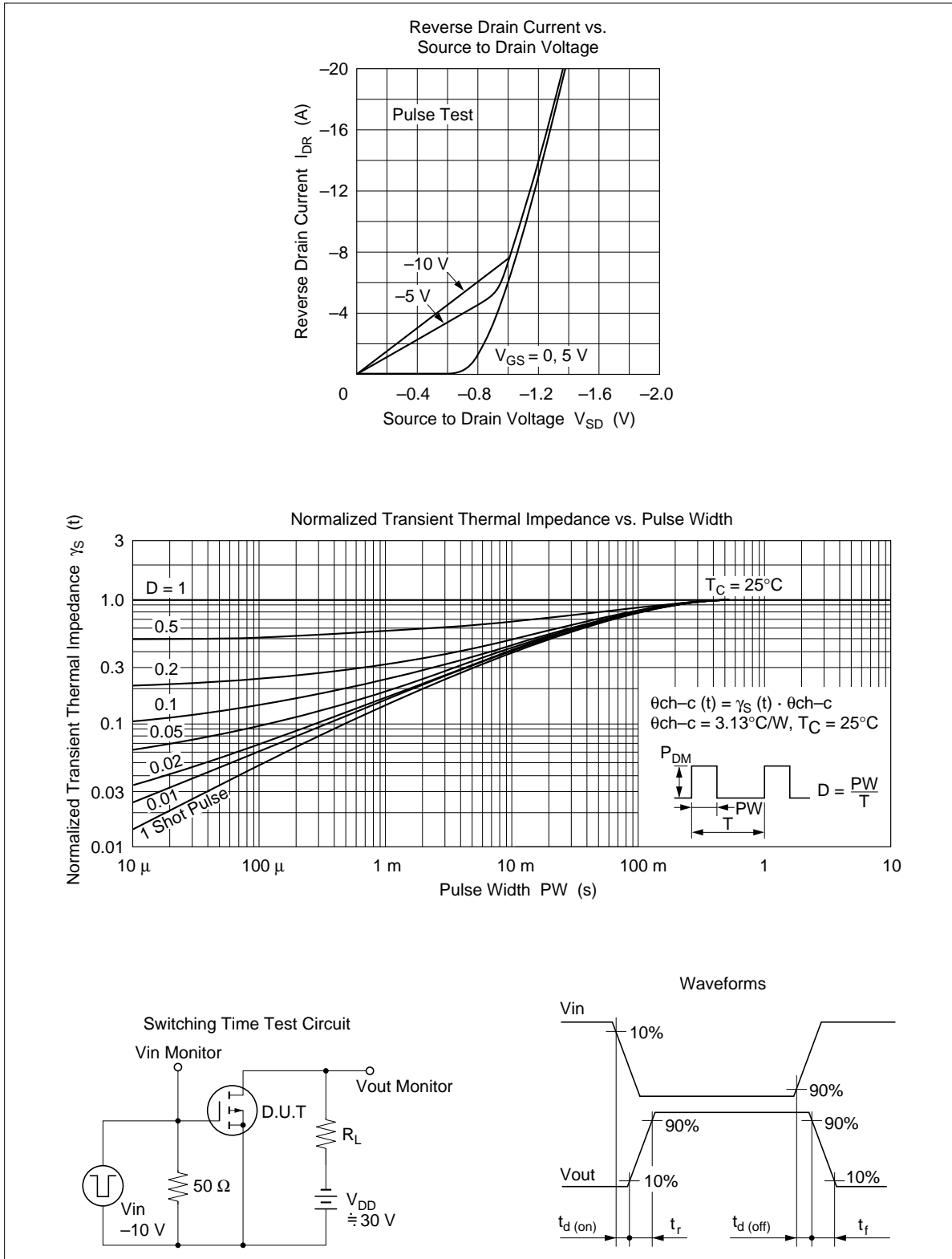
| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|--|---------------|------|------|------|------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | -60 | — | — | V | $I_D = -10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ±20 | — | — | V | $I_G = \pm 100 \mu A$, $V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ±10 | μA | $V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 250 | μA | $V_{DS} = -50 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | -1.0 | — | -2.0 | V | $I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 0.13 | 0.18 | Ω | $I_D = -5 \text{ A}$, $V_{GS} = -10 \text{ V}^{*1}$ |
| | | — | 0.18 | 0.25 | | $I_D = -5 \text{ A}$, $V_{GS} = -4 \text{ V}^{*1}$ |
| Forward transfer admittance | $ y_{fs} $ | 4.0 | 6.5 | — | S | $I_D = -5 \text{ A}$, $V_{DS} = -10 \text{ V}^{*1}$ |
| Input capacitance | Ciss | — | 900 | — | pF | $V_{DS} = -10 \text{ V}$, $V_{GS} = 0$, |
| Output capacitance | Coss | — | 460 | — | pF | f = 1 MHz |
| Reverse transfer capacitance | Crss | — | 130 | — | pF | |
| Turn-on delay time | $t_{d(on)}$ | — | 8 | — | ns | $I_D = -5 \text{ A}$, $V_{GS} = -10 \text{ V}$, |
| Rise time | t_r | — | 65 | — | ns | $R_L = 6 \Omega$ |
| Turn-off delay time | $t_{d(off)}$ | — | 170 | — | ns | |
| Fall time | t_f | — | 105 | — | ns | |
| Body to drain diode forward voltage | V_{DF} | — | -1.1 | — | V | $I_F = -10 \text{ A}$, $V_{GS} = 0$ |
| Body to drain diode reverse recovery time | t_{rr} | — | 200 | — | ns | $I_F = -10 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu s$ |

Note 1. Pulse test









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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071